

# SKT 24,3 Qu ZG bond.



## THYRISTOR

$$I_{T(DC)} = 480 \text{ A}$$

$$V_{RRM} = 1600 \text{ V}$$

Size: 24,3 mm x 24,3 mm

Central gate

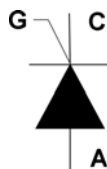
SKT 24,3 Qu ZG bond.

### Features

- high current density due to double mesa technology
- high surge current
- compatible to thick wire bonding
- compatible to all standard solder processes

### Typical Applications\*

- controlled rectifier circuits
- solid state relays



SKT

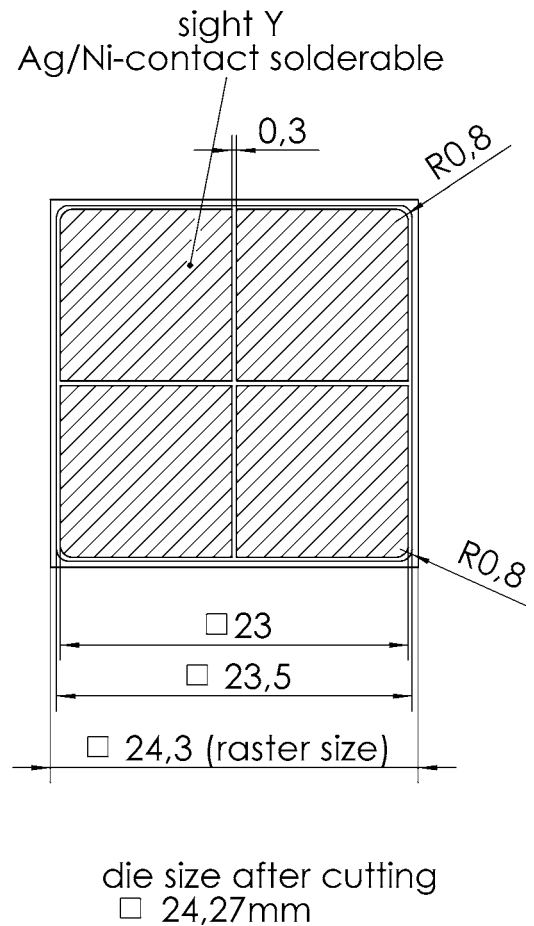
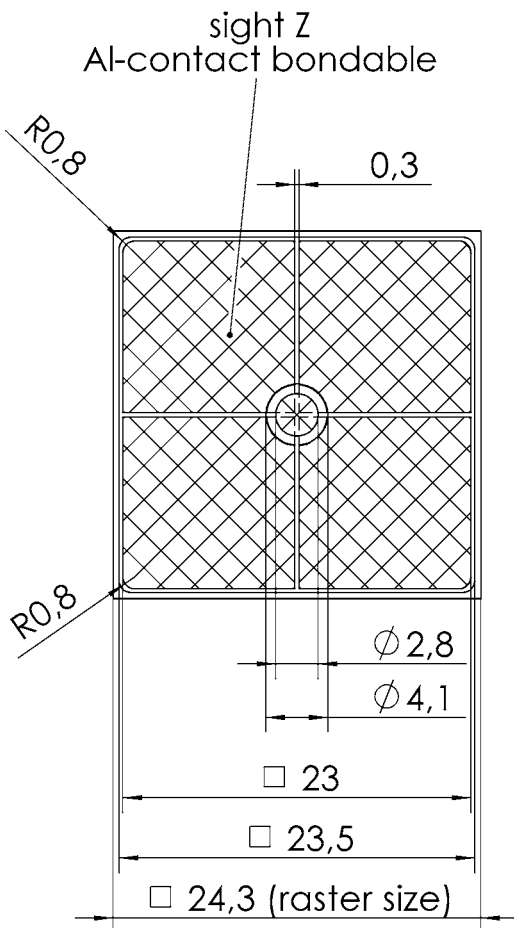
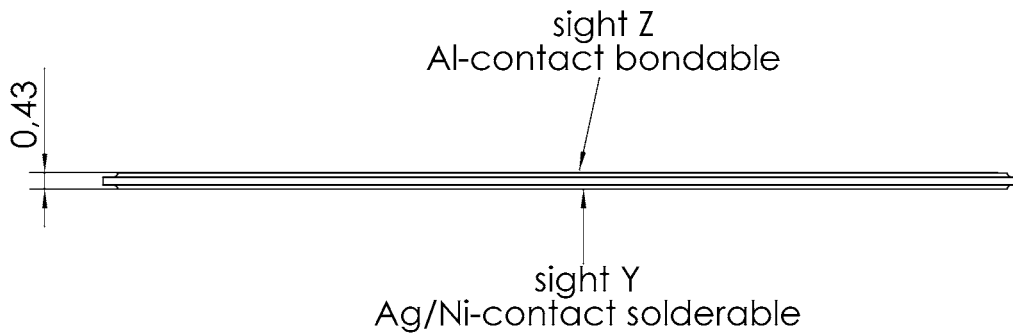
| Absolute Maximum Ratings |  |        |                  |
|--------------------------|--|--------|------------------|
| Symbol                   | Conditions   | Values | Unit             |
| $V_{RRM}$                | $T_j = 25 \text{ }^\circ\text{C}$ ,                                    | 1600   | V                |
| $V_{DRM}$                | $T_j = 25 \text{ }^\circ\text{C}$ , $I_D = 0.5 \text{ mA}$             | 1600   | V                |
| $I_{T(AV)}$              | $T_c = 80 \text{ }^\circ\text{C}$ , $T_j = 130 \text{ }^\circ\text{C}$ | 400    | A                |
| $I_{TSM}$                | $T_j = 130 \text{ }^\circ\text{C}$ , 10 ms, sin 180°                   | 8200   | A                |
| $i^2t$                   | $T_j = 130 \text{ }^\circ\text{C}$ , 10 ms, sin 180°                   | 336200 | A <sup>2</sup> s |
| $T_{jmax}$               |  | 130    | °C               |

| Electrical Characteristics |  |      |      |      |      |
|----------------------------|--|------|------|------|------|
| Symbol                     | Conditions   | min. | typ. | max. | Unit |
| $V_T$                      | $T_j = 130 \text{ }^\circ\text{C}$ , $I_T = 680 \text{ A}$ |      |      | 1.2  | V    |
| $V_{T(TO)}$                | $T_j = 130 \text{ }^\circ\text{C}$                         |      |      | 0.85 | V    |
| $r_T$                      | $T_j = 130 \text{ }^\circ\text{C}$                         |      |      | 0.53 | mΩ   |
| $I_{GT}$                   | $T_j = 25 \text{ }^\circ\text{C}$                          |      |      | 150  | mA   |
| $V_{GT}$                   | $T_j = 25 \text{ }^\circ\text{C}$                          |      |      | 1.98 | V    |
| $I_{GD}$                   | $T_j = 115 \text{ }^\circ\text{C}$                         | 11   |      |      | mA   |
| $V_{GD}$                   | $T_j = 130 \text{ }^\circ\text{C}$                         | 0.25 |      |      | V    |
| $I_H$                      | $T_j = 25 \text{ }^\circ\text{C}$                          |      |      | 220  | mA   |
| $I_L$                      | $T_j = 25 \text{ }^\circ\text{C}$                          |      |      | 550  | mA   |

| Dynamic Characteristics |                                    |      |      |      |      |
|-------------------------|------------------------------------|------|------|------|------|
| Symbol                  | Conditions                         | min. | typ. | max. | Unit |
| $t_q$                   | $T_j = 130 \text{ }^\circ\text{C}$ |      | 150  |      | μs   |
| $(di/dt)_{cr}$          | $T_j = 130 \text{ }^\circ\text{C}$ |      |      | 130  | A/μs |
| $(dv/dt)_{cr}$          | $T_j = 130 \text{ }^\circ\text{C}$ |      |      | 1000 | V/μs |

| Thermal Characteristics |                     |      |       |      |      |
|-------------------------|---------------------|------|-------|------|------|
| Symbol                  | Conditions          | min. | typ.  | max. | Unit |
| $T_j$                   |                     | -40  |       | 130  | °C   |
| $T_{stg}$               |                     | -40  |       | 130  | °C   |
| $T_{solder}$            |                     |      |       | 255  | °C   |
| $R_{th(j-c)}$           | Semipack 3 assembly |      | 0.091 |      | K/W  |

| Mechanical Characteristics |            |                      |                 |
|----------------------------|------------|----------------------|-----------------|
| Symbol                     | Conditions | Values               | Unit            |
| Raster size                |            | 24.3 x 24.3          | mm <sup>2</sup> |
| Area total                 |            | 590                  | mm <sup>2</sup> |
| Anode                      |            | solderable (Ag/Ni)   |                 |
| Gate and Cathode           |            | bondable (Al)        |                 |
| Wire bond                  |            | Al, diameter ≤ 500μm |                 |
| Package                    |            | tray                 |                 |
| Chips / Package            |            | 9                    | pcs             |



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.